**ORIGINAL ARTICLE** 



# Band Structure and Optical Properties of BiOCI: Density Functional Calculation

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#### ABSTRACT

The electronic band structures, density of states (DOS) and optical properties of BiOCl Crystal are investigated using the density functional theory under the local density approximation (LDA). The obtained electronic band structure show that BiOCl crystal has an indirect forbidden band gap of 2.45 eV. The structural optimization for BiOCl has been performed using the LDA. The result of the structure optimization of BiOCl have been compared with the experimental results and have been found to be in good agreement with these results. The linear photon-energy dependent dielectric functions and some optical properties such as the energy-loss function, the effective number of valence electrons and the effective optical dielectric constant are calculated.

Keywords: BiOCl, Ab-inito, band structure, optical properties.

# 1. INTRODUCTION

Bismuth oxychloride (BiOCl), a member of compounds with the general formula  $A_m^V B_n^{VI} X_p^{VII}$ 

(A = As, Sb, Bi; B = O, S, Se

X = Cl, Br, I) is a wide bandgap semiconductor

with a tetragonal PbFCl-type structure (space group  $P_4$ /nmm: No:129) [1,2]. This crystal has 2 BiOCl molecules in a unit cell. Therefore, this compound has a complex structure with 18 valence electrons per unit cell.

The unit cell of BiOCl is shows in Figure 1 [3] and atomic positions in the unit cell are given in Table 1 [1]. The crystal structure can derive from the fluorite (CaF<sub>2</sub>) structure. The Bi atom is coordinated to a square antiprism with four O atoms in one base and four Cl atoms in another. The O atom is tetrahedrally coordinated to four Bi atoms. The Cl atom is bonded with four Bi atom in a planar square to form a pyramid and with its nonbonding (lone pair) electrons pointing to the other side of the square. As shown in the Figure 1, the (BiOCl) layers are stacked together by the nonbonding (van der Waals)

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interaction through the Cl atoms along the c- axist. Therefore, the structure is not closely packed in this direction [3].



Figure 1. The unit cell of BiOCl viewed along (100) [3].

Atoms	X	У	Z
Bi	0.250000	0.250000	0.1714(3)
	0.750000	0.750000	0.828600
0	0.250000	0.750000	0.000000
	0.750000	0.250000	0.000000
Cl	0.250000	0.250000	0.6459(25)
	0.750000	0.750000	0.354100

Table 1. Fractional atomic coordinates (Å) for BiOCl [1]

The electronic structure of BiOCl has been calculated via the tight-binding linear muffin-tin orbital (TB-LMTO) method within the local density approximation (LDA) by Zhang et al. [3] The indirect nature calculated is in agreement with the linear relationship observed experimentally between

 $(\alpha E)^{1/2}$  and E (where  $\alpha$  and E represent the absorption coefficient and photon energy, respectively), although the calculated band gap is relatively narrow [3]. The electronic band structure of BiOX (X=F, Cl, Br and I) have been calculated via DFT method within GGA scheme by Huang at al. [4]. The atomic charges and bond orders have been analyzed using the Mulliken population analysis [5-7], and the spatial distribution of orbital density has also been described [4]. As far as we know, no ab initio general potential calculations of the optical properties of BiOCl have been reported in detail.

In the present work, we have investigated the electronic band structure, the total density of states (DOS), structure optimization and photon energy-dependent optical properties of the BiOCl crystal using a pseudopotential method based on the density functional theory (DFT) in the local density approximation (LDA) [8].

#### 2. COMPUTATIONAL DETAILS

SIESTA (The Spanish Initiative for Electronic Simulations with Thousands of Atoms) code [9-10] was utilized in this study to calculate the energy spectra and optical of BiOCl. It solves the quantum mechanical equation for the electron within DFT approach in the LDA parameterized by Ceperley and Alder [11]. The interactions between electrons and core ions are simulated with seperable Troullier – Martins [12] norm-conserving pseudopotential. The basis set is based on the finite range pseudoatomic orbitals (PAO's) of the Sankey-Nicklewsky type [13], generalized to include multiple-zeta decays.

We have generated atomic pseudopotentials separately for Bi, O and Cl by using the  $6s^26p^3$ ,  $2s^22p^4$  and  $3s^23p^5$  atomic configurations,

respectively. The cut-off radii for present atomic pseudopotentials are taken as s: 3.82 au, p: 2.71 au, d: 2.92au, f: 2.92 au for Bi, 1.43 au for the s, p, d and f channels of O and s: 1.62 au, P: 1.62 au, d:1.84 au, f: 1.84 au for Cl.

SIESTA calculates the self-consistent potantial on a grid in real space. The fineness of this grid is determined in terms of an energy cut-off  $E_c$  in analogy to the energy cut-off when the basis set involves plane waves. Here by using a double-zeta plus polarization (DZP) orbitals basis and the cut-off energies between 50 and 450 Ry with various basis

sets, we found an optimal value of around 300 Ry for BiOCl. For the final computations, 98 k-points for BiOCl were found to be adequate for obtaining the total energy with an accuracy of about 1 meV/atoms.

### 3. RESULTS AND DISCUSSION

#### 3.1. Structural Optimization

All physical properties are related to the total energy. For instance, the equilibrium lattice constant of a crystal is the lattice constant that minimizes the total energy. If the total energy is calculated, any physical property related to the total energy can be determined. Firstly, the equilibrium lattice parameter was computed by minimizing the crystal's total energy calculated for the different values of lattice constant by means of Murnaghan's equation of states (EOS) [14] as in Figure 2, and the result are shown in Table 2 along with the experimental and theoretical values. The lattice parameters for BiOCl are found to be a=b=3.88 (Å) and c=7.314 (Å) for tetragonal structures, and it are in a good agreement with the experimental and theoretical values. In all our calculations we have used the computed lattice parameter.



Figure 2. Energy versus volume curve of BiOCl.

Table 2. Structure parameters of BiOCl materials.

Reference	a (Å)	C (Å)	Space Group	
Present Experimental [1] Experimental [15] Experimental [3] Theory [4]	3.888 3.887 3.888 3.890 3.824	7.314 7.354 7.357 7.890 7.243	P <sub>4</sub> /nmm	

#### 3.2. Electronic Band Structure

The electronic band structures of BiOCl crystals have been calculated along high symmetry directions in the first Brillouin zone (BZ) of the tetragonal system and are shown in Figure 3. The band structures were calculated along the special lines connecting the highsymmetry points  $\Gamma$  (1/2,0,0), X (1/2,0,0), Z(0,0,1/2), M(1/2,1/2,0), R(1/2,0,1/2) and A(1/2,1/2,1/2) in the kspace. The results of the calculations are shown in Figure 4 for BiOCl crystal. In the rightmost panels of this figure, the density of states (DOS) are presented. The calculated band gap values of these crystals are given in Table 3. The valence band in our calculations is composed of the 3s and 3p -states of the Cl, the 2s and 2p –states of the O atom, and the 6s –states of the Bi atom, while the conduction band consists of the 6p –states of the Bi atom.



Figure 3. First Brillouin zone for BiOCl ( space group P<sub>4</sub>/nmm).

Referance	$E_g(eV)$
Present Experimental [3] Theory [4]	<ul><li>2.45 indirect- 2.77 direct</li><li>3.46 indirect</li><li>2.59 indirect</li></ul>

Table 3. Energy band gaps for BiOCl.



Figure 4. Energy band structure and DOS (density of states) for BiOCl.

As can be seen in Figure 4, The top of the valence band positioned near the R point between the Z-R points, and the bottom of the conduction band is located at the nearly midway between the  $\Gamma$  and Z points of the BZ. The band gap of BiOCl is thus indirect with the value 2.45 eV. For BiOCl, the lowest direct band gap value obtained is 2.77 eV.

Finally, the band gap values obtained for BiOCl are less than measured values. For all crystal structures considered, the band gap values are underestimated than the experimental values. This state is caused from the exchange-correlation approximation of DFT.

# **3.3. Optical Properties**

It is well known that the effect of the electric field vector,  $\mathbf{E}(\boldsymbol{\omega})$ , of the incoming light is to polarize the material. At the level of linear response this polarization can be calculated using the following relation [16]:

$$P^{i}(\omega) = \chi_{ij}^{(1)}(-\omega, \omega) \cdot E^{j}(\omega), \qquad (1)$$

Where  $\chi_{ij}^{(1)}$  is the linear optical susceptibility tensor and it is given by [17]

$$\chi_{ij}^{(1)}(-\omega,\omega) = \frac{e^2}{\hbar\Omega} \sum_{nm\vec{k}} f_{nm}(\vec{k}) \frac{r_{nm}^i(\vec{k})r_{mn}^i(\vec{k})}{\omega_{mn}(\vec{k}) - \omega} = \frac{\varepsilon_{ij}(\omega) - \delta_{ij}}{4\pi}$$
(2)

Where n, m denote energy bands,  $f_{mn}(\vec{k}) \equiv f_m(\vec{k}) - f_n(\vec{k})$  is the fermi occupation factor,  $\Omega$  is the normalization volume.  $\omega_{mn}(\vec{k}) \equiv \omega_m(\vec{k}) - \omega(\vec{k})$  are the frequency differences,  $\hbar \omega_n(\vec{k})$  is the energy of band n at wavevector **k**. The  $\vec{r}_{nm}$  are the matrix elements of the position operator and are give by

$$r_{nm}^{i}(\vec{k}) = \frac{v_{nm}^{i}(\vec{k})}{i\omega_{nm}}; \quad \omega_{n} \neq \omega_{m}$$
(3)

$$r_{nm}^i(k) = 0; \quad \omega_n = \omega_n$$

Where  $v_{nm}^{i}(\vec{k}) = m^{-1}p_{nm}^{i}(\vec{k}), m$  is the free electron mass, and  $\vec{p}_{nm}$  is the momentum matrix element.

As can be seen from equation (2), the dielectric function  $\varepsilon_{ij}(\omega) = 1 + 4\pi \chi_{ij}^{(1)}(-\omega, \omega)$  and the imaginary part of  $\varepsilon_{ij}(\omega)$ ,  $\varepsilon_2^{ij}(\omega)$ , is given by

$$\varepsilon_{2}^{ij}(w) = \frac{e^{2}}{\hbar\pi} \sum_{nm} \int d\vec{k} fnm(\vec{k}) \frac{v_{nm}^{i}(\vec{k})v_{nm}^{j}(\vec{k})}{\omega_{mn}^{2}} \delta(\omega - \omega_{mn}(\vec{k})).$$

$$\tag{4}$$

The real part of  $\varepsilon_{ij}(\omega), \varepsilon_1^{ij}(\omega)$ , can be obtained by using the Kramers-Kroning transformation

$$\varepsilon_1^{ij}(\omega) - 1 = \frac{2}{\pi} \wp \int_0^\infty \frac{\omega' \varepsilon_2^{ij}(\omega')}{{\omega'}^2 - {\omega}^2} d\omega'.$$
(5)

Because the Kohn-Sham equations determine the ground state properties, the unoccupied conduction bands as calculated have no physical significance. If they are used as single-particle states in a calculation of optical properties for semiconductors, a band gap problem comes into included in calculations of response. In order to take into account self-energy effects, in the present work, we used the 'scissors approximation' [16].

In the present work,  $\Delta$ , the scissor shift to make the theoretical band gap match the experimental one, is 1.01 eV for BiOCl.

Expressions for the energy-loss spectrum,  $L(\omega)$ 

$$L_{ij}(\omega) = -\operatorname{Im} \varepsilon_{ij}^{-1}(\omega), \tag{6}$$

The known sum rules [18] can be used to determine some quantitative parameters, particularly the effective number of the valence electrons per unit cell  $N_{eff}$ , as well as the effective optical dielectric constant  $\varepsilon_{eff}$ , which make a contribution to the optical constants of a crystal at the energy  $E_0$ . One can obtain an estimate of the distribution of oscillator strengths for both intraband and interband transitions by computing the  $N_{eff}(E_0)$  defined according to

$$N_{eff}(E) = \frac{2m\varepsilon_0}{\pi\hbar^2 e^2 Na} \int_0^\infty \varepsilon_2(E) E dE, \qquad (7)$$

Where  $N_a$  is the density of atoms in a crystal, e and m are the charge and mass of the electron, respectively and  $N_{eff}(E_0)$  is the effective number of electrons contributing to optical transitions below an energy of  $E_0$ .

Further information on the role of the core and semicore bands may be obtained by computing the contribution which the various bands make to the static dielectric constant,  $\mathcal{E}_0$ .

According to the Kramers-Kronig relations, one has

$$\varepsilon_0(E) - 1 = \frac{2}{\pi} \int_0^\infty \varepsilon_2(E) E^{-1} dE.$$
(8)

One can therefore define an 'effective' dielectric constant, which represents a different mean of the interband transitions from that represented by the sum rule, equation (8), according to the relation

$$\varepsilon_{eff}(E) - 1 = \frac{2}{\pi} \int_{0}^{E_{0}} \varepsilon_{2}(E) E^{-1} dE.$$
 (9)

The physical meaning of  $\mathcal{E}_{eff}$  is quite clear:  $\mathcal{E}_{eff}$  is the effective optical dielectric constant governed by the interband transitions in the energy range from zero to  $E_0$ , i.e. by the polarizition of the electron shells.

In order to calculate the optical response by using the calculated band structure, we have chosen a photonenergy range of 0-30 eV and have seen that a 0-18 eV photon-energy range is sufficient for most optical functions.

The BiOCl crystal has an tetragonal structure that is optically uniaxial system. For this reason, the linear dielectric tensor of the BiOCl crystal has two independent components that are the diagonal elements of the linear dielectric tensor. The calculated real parts and imaginary parts of the xx- and zz- components of the linear frequency- dependent dielectric function are presented in Figure 5. The function  $\varepsilon_1^{xx}$  is equal to zero at about 6.66 eV, 10.72 eV, 13.90 eV, 22.5 eV , 22.99 eV and 23.23 eV (at the W, X, Y, Z, U and V in Figure 5), while the other function  $\varepsilon_1^{zz}$  is equal to zero at about 7.37 eV, 8.35 eV, 8.49 eV, 9.90 eV, 12.97 eV and 22.28 eV (at the W, X, Y, Z, U and V in Figure 5). The values of the  $\varepsilon_2^{xx}$  and  $\mathcal{E}_2^{zz}$  peaks shown in Figure 5 are summarized in Table 4. This peaks correspond to the transitions from the valence to the conduction band (see Figure 5).

E2 A B C D E F G H I J K L M	N O P
xx 5.44 6.39 7.21 11.53 12.49 13.49 14.93 15.61 16.21 17.66 18.47 18.93 20.7	3 21.95 22.91 24.02
zz 4.97 6.04 7.26 8.65 10.39 12.87 14.06 15.02 15.51 16.29 17.85 18.93 19.5	9 20.21 23.61 24.87

Table 4. Comparative characteristics of linear optical functions of BiOCl crystal.



Figure 5. Energy spectra of dielectric function  $\varepsilon = \varepsilon_1 - i\varepsilon_2$  for BiOCl.

The calculated energy-loss functions,  $L(\omega)$ , are presented in Figure 6. In this figure,  $L_{xx}$  and  $L_{zz}$ correspond to the energy-loss functions along the x- and z- directions, respectively. The function  $L(\omega)$ describes the energy loss of fast electrons traversing the material. The sharp maxima in the energy-loss function are associated with the existence of plasma oscillations [19]. The curves of  $L_{xx}$  and  $L_{zz}$  in Figure 6 have a maximum near 24.33 and 25.23 eV, respectively and these value coincide with the V point in Figure 5.



The calculated effective number of valence electrons  $(N_{eff})$  and the effective dielectric constant  $(\varepsilon_{eff})$ are given in Figure 7. The effective number of valence electron per unit cell,  $N_{\it eff}$  , contributing in the interband transitions, reaches saturation value at about 26 eV. This means that deep-lying valence orbitals paticipate in the interband transitions as well (see Figure 4)

The effective optical dielectric constant,  $\,\mathcal{E}_{e\!f\!f}$  , shown in Figure 7, reaches a saturation value at about 16 eV. The photon-energy dependence of  $\mathcal{E}_{eff}$  can be separated into two regions. The first is characterized by a rapid rise and it extends up to  $10 \ eV$ . In the second region the value of  $\mathcal{E}_{eff}$  rises more smoothly and slowly and tends to saturation at the energy 16  $\,eV$  . This means that the greatest conribution to  $\varepsilon_{e\!f\!f}$  arises from interband transitions between 4.7 and 16  $\,eV$  .



Figure 7. Energy spectra of  $N_{eff}$  and  $\mathcal{E}_{eff}$  along the x- and z- axes.

### 4. CONCLUSIONS

In present work, we have made a detailed investigation of the electronic structure and frequency-dependent linear optical properties of the BiOCl crystal using the density functional methods. The task of this work was to apply the density-functional methods to a complex crystal like the BiOCl. It is seen that BiOCl crystal have the indirect forbidden gap. The obtained band gap values are in agreement with the previous results. The total DOS calculation shows that the valence band is composed of 3s and 3p states of the Cl atom, 2s and 2p states of the O atom and 6s states of the Bi atom while the conduction band consists of 6p states of the Bi atom. we have examined photon energy dependent dielectric functions as well as related quantities such as energyloss function, the effective number of valence electrons per unit cell participating in the interband transitions and the effective optical dielectric function along the xand z- axes. The results of the structural optimization implemented using the LDA are in excellent agreement with the experimental results. To our knowledge, this is the first detailed study of the optical properties of BiOCl.

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